

ABSTRACT OF THE DISCLOSURE

A gallium nitride compound semiconductor light emission device includes: a substrate; an n-type electrode region comprising an n-type transmissive electrode; a gallium nitride compound semiconductor multilayer structure including an active layer; and a p-type electrode region comprising a p-type transmissive electrode. The p-type transmissive electrode and the n-type transmissive electrode transmit light which is generated in the active layer and reflected from the substrate so that the light exits the light emission device.

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